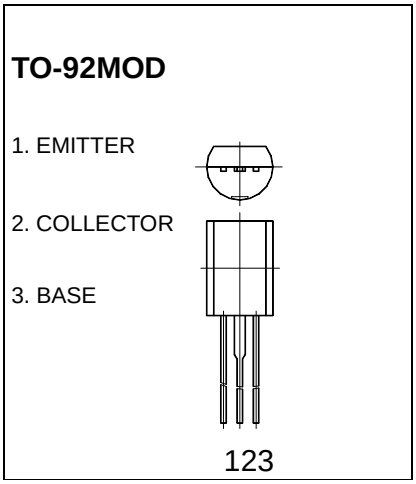
Transys Electronics LIMITED

TO-92MOD Plastic-Encapsulated Transistors

2SC2060 TRANSISTOR (NPN)



FEATURE

Power dissipation

P_{CM}: 0.75 W (Tamb=25℃)

Collector current

I_{CM}: 1 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA , I_E=0	40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1mA , I_B=0	32		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=40V , I_E=0		0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V , I_C=0		0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=3V, I_C= 100mA	80	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 500m A, I_B= 50mA		0.4	V